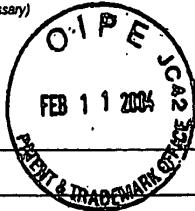


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		Application Number	09/945535
		Filing Date	August 30, 2001
		First Named Inventor	Ahn, Kie
		Group Art Unit	2813
		Examiner Name	Blum, David
Sheet 1 of 1		Attorney Docket No: 1303.026US1	



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Examiner Initials*	USP Document Number	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	Filing Date If Appropriate
/SN	US-2001/0009695	07/26/2001	Saanila, Ville A., et al.	427	255.39	01/18/2001
	US-2002/0146916	10/10/2002	Irino, Kiyoshi, et al.	438	785	03/29/2002
	US-2003/0175411	09/18/2003	Kodas, T. T., et al.	427	58	10/04/2002
	US-6,093,944	07/25/2003	VanDover, R B.	257	310	06/04/1998
✓	US-6,451,695	09/17/2002	Sneh, O.	438	685	12/22/2000
✓	US-6,602,338	08/05/2003	Chen, S., et al.	106	287.19	04/11/2001

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Examiner Initials*	Foreign Document No	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	T ²

OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS						
Examiner Initials*	Cite No ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.				
/SN		CHAMBERS, J J., et al., "Physical and electrical characterization of ultrathin yttrium silicate insulators on silicon", <u>Journal of Applied Physics</u> , 90(2), (July 15, 2001), 918-33				
		KUKLI, KAUPO, et al., "Low-Temperature Deposition of Zirconium Oxide-Based Nanocrystalline Films by Alternate Supply of Zr[OC(CH ₃) ₃] ₄ and H ₂ O", <u>Chemical Vapor Deposition</u> , 6(6), (2000), 297-302				
		NAKAJIMA, ANRI, "Soft breakdown free atomic-layer-deposited silicon-nitride/SiO ₂ stack gate dielectrics", <u>International Electron Devices Meeting, Technical Digest</u> , (2001), 6.5.1-4				
		RAHTU, ANTTI, et al., "Atomic Layer Deposition of Zirconium Titanium Oxide from Titanium Isopropoxide and Zirconium Chloride", <u>Chemistry of Materials</u> , 13(5), (May 2001), 1528-1532				
✓		WOLF, S., et al., In: <u>Silicon Processing of the VLSI Era</u> , Vol. 1, Lattice Press, 374-380				

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		<table border="1"> <tr> <td>Application Number</td> <td colspan="4">09/945535</td> </tr> <tr> <td>Filing Date</td> <td colspan="4">August 30, 2001</td> </tr> <tr> <td>First Named Inventor</td> <td colspan="4">Ahn, Kie</td> </tr> <tr> <td>Group Art Unit</td> <td colspan="4">2813</td> </tr> <tr> <td>Examiner Name</td> <td colspan="4">Blum, David</td> </tr> </table>					Application Number	09/945535				Filing Date	August 30, 2001				First Named Inventor	Ahn, Kie				Group Art Unit	2813				Examiner Name	Blum, David			
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Substitute Disclosure Statement Form (PTO-1449)

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